TECHNICAL DATA DATA SHEET 623, REV -

HERMETIC POWER MOSFET N-CHANNEL

FEATURES:

- 600 Volt, 0.35 Ohm MOSFET
- Isolated and Hermetically Sealed
- Surface Mount Package
- Electrically equivalent to IXTM20N60

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_{_{\Delta}}$ = 25°C UNLESS OTHERWISE SPECIFIED.

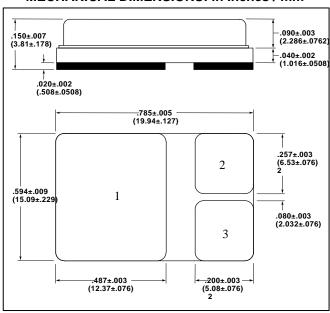
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
CONTINUOUS DRAIN CURRENT V _{GS} =10V, T _C = 25°C	I _D	-	-	20	Amps
PULSED DRAIN CURRENT @ $T_c = 25$ °C	I _{DM}	-	-	80	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	0.27	°C/W
TOTAL DEVICE DISSIPATION @ T _C = 25°C	P _D	-	-	450	Watts

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV _{DSS}	600	-	-	Volts
$V_{GS} = 0V, I_D = 250\mu A$					
DRAIN TO SOURCE ON STATE RESISTANCE		-	-		Ω
$V_{GS} = 10V, I_{D} = 10A$	R _{DS(ON)}			0.35	
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = 250 \mu A$	$V_{GS(th)}$	2.0	-	4.5	Volts
FORWARD TRANSCONDUCTANCE	g fs	11	18	-	S(1/Ω)
$V_{DS} = 10V, I_{D} = 10A$					
ZERO GATE VOLTAGE DRAIN CURRENT, T _J = 25°C	I _{DSS}	-	-	250	
$(V_{DS} = 0.8xMax. Rating, V_{GS} = 0V), T_{J} = 125^{\circ}C$				1000	μΑ
GATE TO SOURCE LEAKAGE FORWARD V _{GS} = 20V	I _{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE V _{GS} = -20V				-100	
TOTAL GATE CHARGE $V_{GS} = 10 \text{ V}$,	Q_g	-	150	170	
GATE TO SOURCE CHARGE $V_{DS} = 300V$,	Q_{gs}		29	40	nC
GATE TO DRAIN CHARGE $I_D = 10A$	Q_gd		60	85	
TURN ON DELAY TIME $V_{DS} = 300V$,	$t_{d(ON)}$	-	20	40	
RISE TIME $I_D = 10A$,	t _r		43	60	nsec
TURN OFF DELAY TIME $R_G = 2.0\Omega$,	$t_{d(OFF)}$		70	90	
FALL TIME $V_{GS} = 10V$	t _f		40	60	
DIODE FORWARD VOLTAGE $T_J = 25^{\circ}C$, $I_F = I_S$	V_{SD}	-	-	1.5	Volts
$V_{GS} = 0V$					
REVERSE RECOVERY TIME $T_J = 25^{\circ}C$,	t _{rr}	-	600	-	nsec
$I_{F} = I_{S},$					
di/dt ≤ = 100A/μsec	_				
INPUT CAPACITANCE $V_{GS} = 0V, V_{DS} = 25V,$	C_{iss}	-	4500	-	_
OUTPUT CAPACITANCE f=1MHz	C _{oss}		420		pF
REVERSE TRANSFER CAPACITANCE	C_{rss}		140		

DATA SHEET 623 REVISION -

MECHANICAL DIMENSIONS: in Inches / mm



SHD-6

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
MOSFET	DRAIN	SOURCE	GATE
SHD-6 PACKAGE			

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